



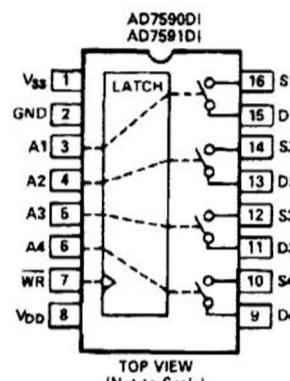
DI CMOS  
Analog Switches with Data Latches  
**AD7590DI/AD7591DI/AD7592DI**

**FEATURES**

SCR Latch-Proof  
Overvoltage-Proof:  $\pm 25V$   
Low Ron:  $60\Omega$ typ  
Buffered Switch Logic  
TTL, CMOS Compatible  
Monolithic Dielectrically-Isolated CMOS  
Pin Compatible with AD75100I Series

**FUNCTIONAL BLOCK DIAGRAMS**

**16-Pin DIP**



TOP VIEW  
(Not to Scale)

AD7590DI  
AD7591DI

LATCH

S1 S2 S3 S4

D1 D2 D3 D4

A1 A2 A3 A4

WR VDD VSS GND

TOP VIEW  
(Not to Scale)

AD7590DI  
AD7591DI

LATCH

S1 S2 S3 S4

D1 D2 D3 D4

A1 A2 A3 A4

WR VDD VSS GND

TOP VIEW  
(Not to Scale)

AD7592DI

LATCH

S1 OUT1 OUT2

S2 S4 S3 NC

NC NC NC NC

VDD VSS GND A1 A2 A3 A4 NC

TOP VIEW  
(Not to Scale)

AD7592DI

LATCH

S1 OUT1 OUT2

S2 S4 S3 NC

NC NC NC NC

VDD VSS GND A1 A2 A3 A4 NC

TOP VIEW  
(Not to Scale)

AD7592DI

**CONTROL LOGIC (WR HELD LOW)**

AD7590DI: Switch "ON" for Address "HIGH"

AD7591DI: Switch "ON" for Address "LOW"

AD7592DI: Address "HIGH" makes S1 to Out 1 and S3 to Out 2

**REV. A**

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Telex: 924491 Cable: ANALOG NORWOODMASS

## AD7590DI/AD7591DI/AD7592DI—SPECIFICATIONS ( $V_{DD} = 15V$ , $V_{SS} = -15V$ unless otherwise noted)

Parameter	Model	$T_A = +25^\circ C$ (K, B, T)	$T_A =$ 0 to $+70^\circ C$ (K) $-25^\circ C$ to $+85^\circ C$ (B)	$-55^\circ C$ to $+125^\circ C$ (T)	Units	Test Conditions/Comments
<b>ANALOG SWITCH</b>						
Analog Signal Range	All	$\pm 10$	$\pm 10$	$\pm 10$	Volts	
$R_{ON}$ <sup>1</sup>	All	60			$\Omega$ typ	$-10V \leq V_S \leq +10V$ , $I_{DS} = 1mA$
	All	90	120	150	$\Omega$ max	Test Circuit 1
$R_{ON}$ Match <sup>2</sup>	All	2			$\Omega$ typ	$V_S = 0$ , $I_{DS} = 1mA$
$R_{ON}$ Match Drift <sup>2</sup>	All	0.01			$\Omega/C$ typ	$V_S = 0$ , $I_{DS} = 1mA$
$I_{D,OFF}$ <sup>1</sup>	AD7590DI	0.5			nA typ	Test Circuit 2
	AD7591DI	5	50	200	nA max	
$I_{S,OFF}$ <sup>1</sup>	All	0.5	50	200	nA typ	Test Circuits 2 & 4
		5			nA max	
$I_D$ ( $I_S$ )ON <sup>1</sup>	All	0.5	50	200	nA typ	Test Circuit 3
		5			nA max	
$I_{OUT}$ <sup>1</sup>	AD7592DI	1	50	200	nA typ	Test Circuit 4
		10	100	400	nA max	
$C_S(C_D)OFF$ <sup>3</sup>	All	10			pF typ	
$C_S(C_D)ON$ <sup>3</sup>	All	30			pF typ	
$C_{DS}(C_{S,OFF})$	All	1			pF typ	
$C_{DD}(C_{SS})$ <sup>3</sup>	All	0.5			pF typ	
$C_{OUT}$ <sup>3</sup>	AD7592DI	40			pF typ	
<b>DIGITAL CONTROL</b>						
$V_{INH}$ <sup>1</sup>	All	0.8	0.8	0.8	V max	
$V_{INH}$ <sup>1</sup>	All	2.4	2.4	2.4	V min	
$C_{IN}$ <sup>3</sup>	All	7	7	7	pF typ	
$I_{INL}$ or $I_{INH}$ <sup>1,4</sup>	All	1	1	1	$\mu A$ max	$V_{IN} = 0$ or $V_{DD}$
<b>DYNAMIC CHARACTERISTICS</b>						
$t_{ON}$ <sup>2</sup>	AD7590DI	250	380	380	ns max	Test Circuit 5
	AD7591DI	400	500	500	ns max	
$t_{OFF}$ <sup>2</sup>	AD7590DI	400	500	500	ns max	Test Circuit 5
	AD7591DI	250	380	380	ns max	
$t_{TRANSITION}$ <sup>2</sup>	AD7592DI	350	450	450	ns max	Test Circuit 6
Write Pulse Width ( $t_{WR}$ ) <sup>2</sup>	All	250	300	400	ns min	See Figure 1
Address Setup Time ( $t_{AS}$ ) <sup>2</sup>	All	300	300	400	ns min	See Figure 1
Address Hold Time ( $t_{AH}$ ) <sup>2</sup>	All	20	30	40	ns min	See Figure 1
Off Isolation <sup>4</sup>					dB typ	A, $\overline{WR} = 0.8V$ ; $V_S = 10V$ (Pk-Pk); $f = 1kHz$ , $R_L = 10k\Omega$
(Analog Input to Analog Output)	All	-85			mV peak, typ	$R_L = 1M\Omega$ , $C_L = 15pF$ ; $V_{INH} = 3V$ , $V_{INL} = 0V$ ; $t_{RISE} = t_{FALL} = 20ns$ ; $\overline{WR}$ held HIGH
Crosstalk <sup>3</sup>						
(Digital Input to Analog Output)	All	5				
$Q_{INJ}$ <sup>3</sup>	All	55			pC typ	Test Circuit 7
<b>POWER SUPPLY</b>						
$I_{DD}$ <sup>1</sup>	All	1	1.5	2	$mA$ max	
$I_{SS}$ <sup>1</sup>	All	1	1	1	$mA$ max	Digital Inputs = $V_{INL}$ or $V_{INH}$

NOTES

<sup>1</sup>100% tested.

<sup>2</sup>Guaranteed, not production tested.

<sup>3</sup>Typical values for information only, not subject to test.

<sup>4</sup>Inputs are MOS gates typical current less than 10nA.

Specifications subject to change without notice.

### TIMING AND CONTROL SEQUENCE

Figure 1 shows the timing sequence for latching the switch address inputs. The latches are level sensitive and, therefore, while  $\overline{WR}$  is held low the latches are transparent and the switches respond to the address inputs. The digital inputs are latched on the rising edge of  $\overline{WR}$ .

NOTE: All digital input signals rise and fall times measured from 10% to 90% of 3V.  $t_R = t_F = 20ns$ .

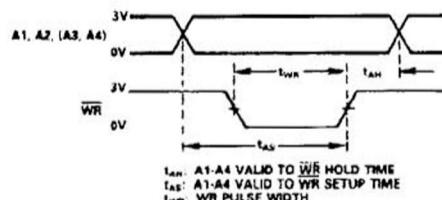


Figure 1. Timing and Control Sequence

## AD7590DI/AD7591DI/AD7592DI

### **ABSOLUTE MAXIMUM RATINGS\***

( $T_A = +25^\circ\text{C}$  unless otherwise noted)

V <sub>DD</sub> to GND . . . . .	+17V
V <sub>SS</sub> to GND . . . . .	-17V
Overvoltage at V <sub>D</sub> (V <sub>S</sub> ), One Switch Only (1sec surge) . . . . .	V <sub>DD</sub> +25V or V <sub>SS</sub> -25V
(Continuous) . . . . .	V <sub>DD</sub> +20V or V <sub>SS</sub> -20V or 20mA, Whichever Occurs First
Switch Current (I <sub>DS</sub> , Continuous) . . . . .	50mA
Switch Current (I <sub>DS</sub> , Surge) 1ms Duration, 10% Duty Cycle . . . . .	150mA
Digital Input Voltage Range . . . . .	-0.3V to V <sub>DD</sub> +0.3V
Power Dissipation (Any Package) Up to +75°C . . . . .	450mW
Derates above +75°C by . . . . .	6mW/C
Storage Temperature . . . . .	-65°C to +150°C
Operating Temperature Plastic (KN Versions) . . . . .	0 to +70°C
Cerdip (BQ Versions) . . . . .	-25°C to +85°C
Cerdip (TQ Versions) . . . . .	-55°C to +125°C

\*Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **CAUTION:**

ESD (electrostatic discharge) sensitive device. The digital control inputs are diode protected; however, permanent damage may occur on unconnected devices subject to high energy electrostatic fields. Unused devices must be stored in conductive foam or shunts. The protective foam should be discharged to the destination socket before devices are inserted.



### **ORDERING GUIDE**

Model <sup>1</sup>	Temperature Range	Package Option <sup>2</sup>
AD7590DIKN	0°C to +70°C	N-16
AD7590DIKP	0°C to +70°C	P-20A
AD7590DIBQ	-25°C to +85°C	Q-16
AD7590DITQ	-55°C to +125°C	Q-16
AD7591DIKN	0°C to +70°C	N-16
AD7591DIKP	0°C to +70°C	P-20A
AD7591DIBQ	-25°C to +85°C	Q-16
AD7591DITQ	-55°C to +125°C	Q-16
AD7592DIKN	0°C to +70°C	N-14
AD7592DIKP	0°C to +70°C	P-20A
AD7592DIBQ	-25°C to +85°C	Q-14
AD7592DITQ	-55°C to +125°C	Q-14

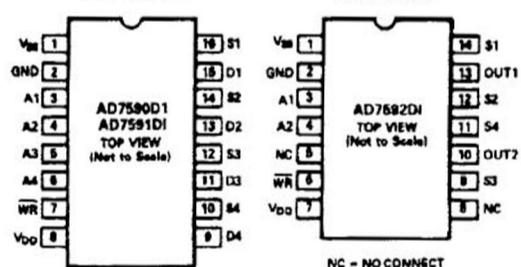
### **NOTES**

<sup>1</sup>To order MIL-STD-883C, Class B processed parts, add /883B to part number. Refer to the Analog Devices Military Products Databook (1990) for military data sheet.

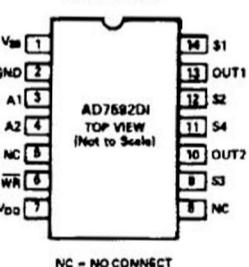
<sup>2</sup>N = Narrow Plastic DIP; P = Plastic Leaded Chip Carrier Q = Cerdip. For Hermetic Surface Mount package, contact your local sales office.

### **PIN CONFIGURATIONS**

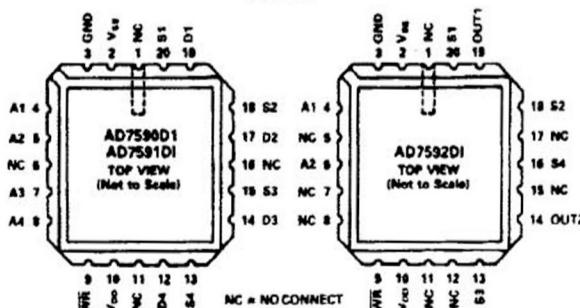
#### **16-Pin DIP**



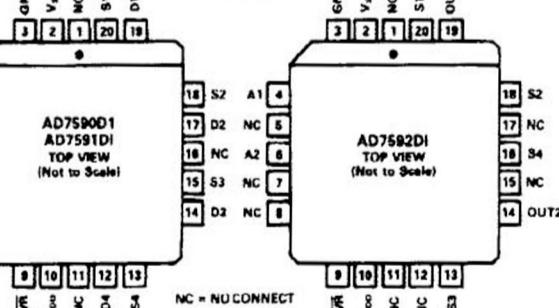
#### **14-Pin DIP**



#### **LCCC**



#### **PLCC**



## AD7590DI/AD7591DI/AD7592DI

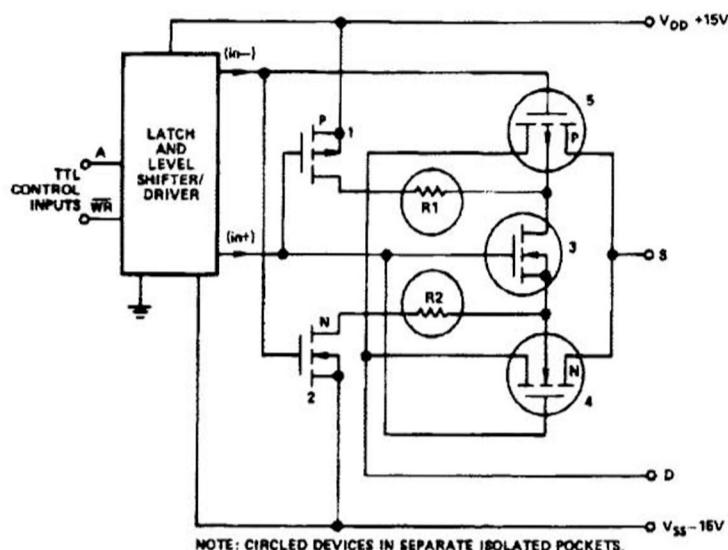


Figure 2. Typical Output Switch Circuitry of AD7590DI Series

### CIRCUIT DESCRIPTION

CMOS devices make excellent analog switches; however, problems with overvoltage and latch-up phenomenon necessitated protection circuitry. These protection circuits, however, either caused degradation of important switch parameters such as  $R_{ON}$  or leakage, or provided only limited protection in the event of overvoltage.

The AD7590DI series switches utilize a dielectrically-isolated CMOS fabrication process to eliminate the four-layer substrate found in junction-isolated CMOS, thus providing latch-free operation.

A typical switch channel is shown in Figure 2. The output switching element is comprised of device numbers 4 and 5. Operation is as follows: for an "ON" switch, (in +) is  $V_{DD}$  and (in -) is  $V_{SS}$  from the driver circuits. Device numbers 1 and 2 are "OFF" and number 3 is "ON". Hence, the backgates of the P- and N-channel output devices (numbers 4 and 5) are tied together and floating. The circled devices are located in separate dielectrically isolated pockets. Floating the output switch backgates with the signal input increases the effective threshold voltage for an applied analog signal, thus providing a flatter  $R_{ON}$  versus  $V_S$  response.

For an "OFF" switch, device number 3 is "OFF," and the backgates of devices 4 and 5 are tied through  $1k\Omega$  resistors (R1 and R2) to the respective supply voltages through the "ON" devices 1 and 2.

If a voltage is applied to the S or D (OUT) terminal which exceeds  $V_{DD}$  or  $V_{SS}$ , the S- or D-to-backgate diode is forward biased; however, R1 and R2 provide current limiting action to the supplies.

An equivalent circuit of the output switch element in Figure 3 shows that, indeed, the  $1k\Omega$  limiting resistors are in series with the backgates of the P- and N-channel output devices – not in series with the signal path between the S and D terminals.

It is possible to turn on an "OFF" switch by applying a voltage in excess of  $V_{DD}$  or  $V_{SS}$  to the S or D terminal. If a positive stress voltage is applied to the S or D terminal which exceeds  $V_{DD}$  by a threshold, then the P-channel (device 5) will turn on creating a low impedance path between the S and D terminals. A similar situation exists for negative stress voltages which exceed  $V_{SS}$ . In this case the N-channel provides the low impedance path between the S and D terminals. The limiting factor on the overvoltage protection is the power dissipation of the package and is  $\pm 20V$  continuous (or 20mA whichever occurs first) above the supply voltages.

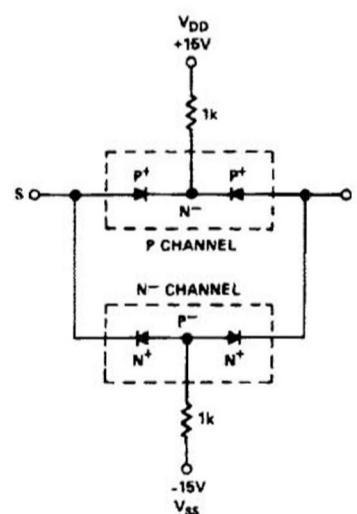
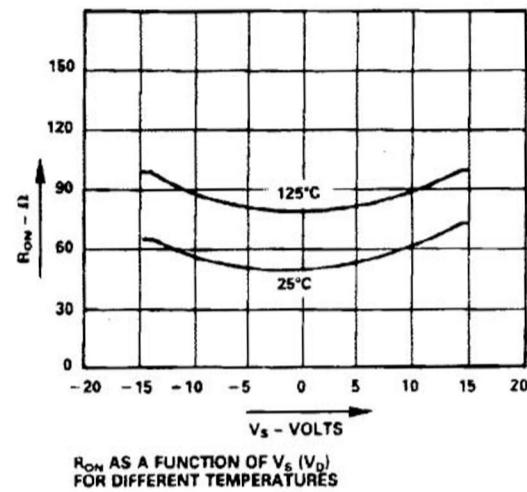
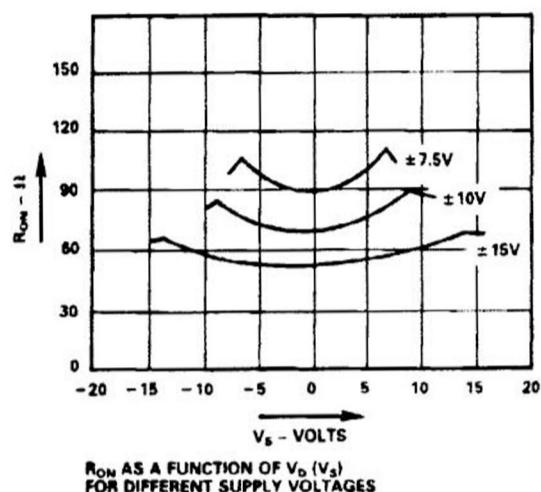


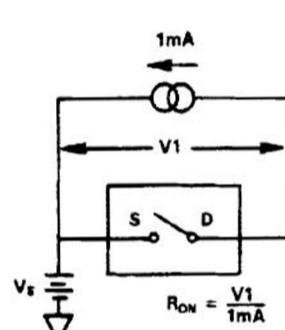
Figure 3. AD7590DI Series Output Switch Diode-Equivalent Circuit

## AD7590DI/AD7591DI/AD7592DI

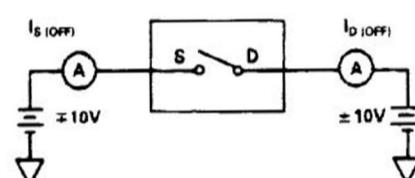
### Typical Performance Characteristics and Test Circuits



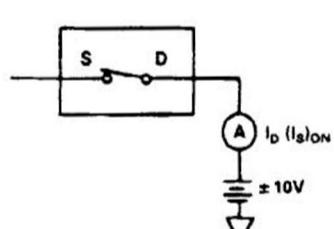
TEST CIRCUIT 1



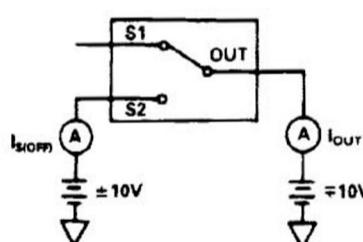
TEST CIRCUIT 2  
(AD7590DI, AD7591DI)



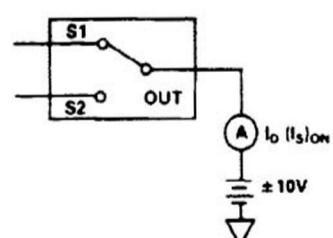
TEST CIRCUIT 3



TEST CIRCUIT 4  
(AD7592DI ONLY)



a. AD7590DI, AD7591DI



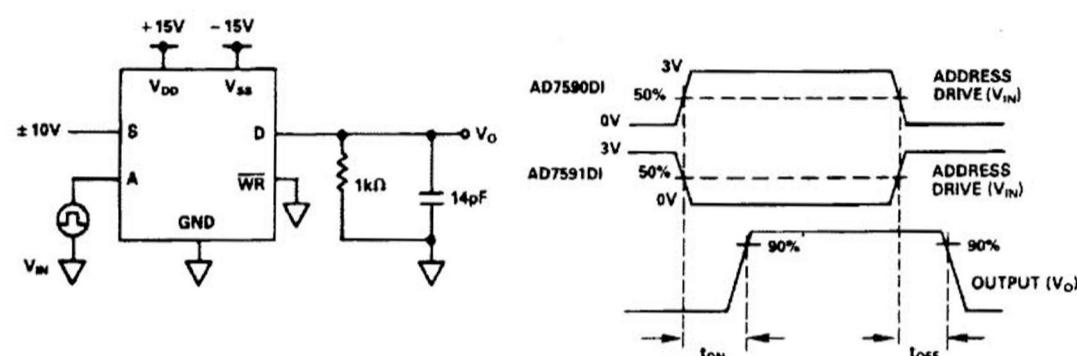
b. AD7592

## AD7590DI/AD7591DI/AD7592DI

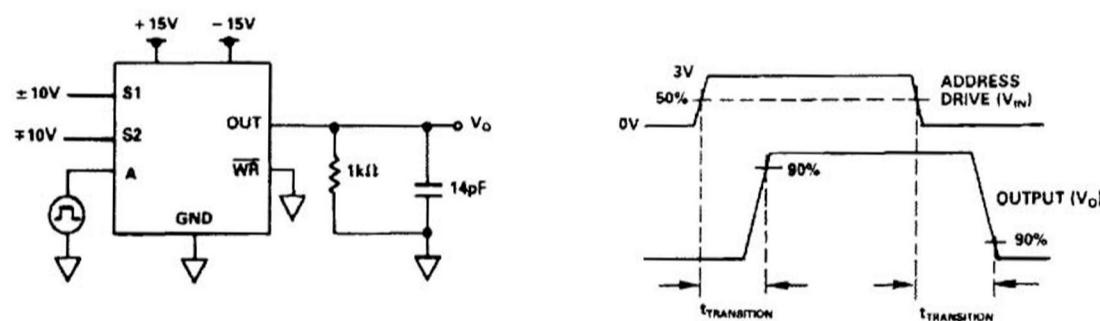
### Typical Switching Characteristics and Test Circuits

Note: All digital input signal rise and fall times measured from 10% to 90% of 3V.  $t_r = t_f = 20\text{ns}$ .

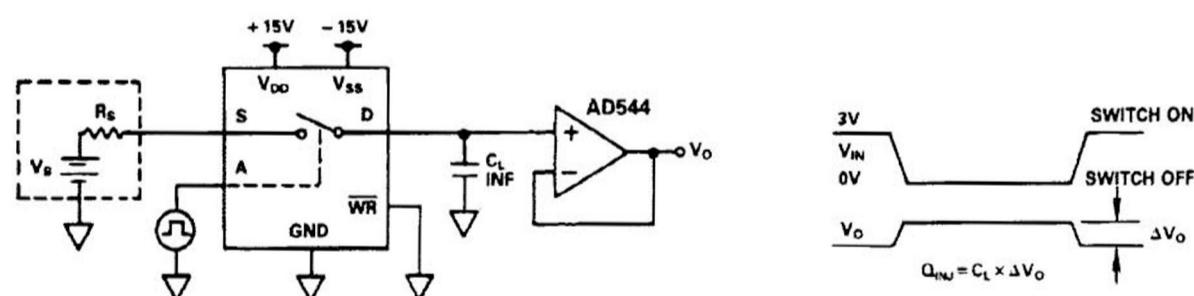
**TEST CIRCUIT 5**  
SWITCHING TIME OF AD7590DI AND AD7591DI,  $t_{ON}$ ,  $t_{OFF}$



**TEST CIRCUIT 6**  
SWITCHING TIME OF AD7592DI,  $t_{TRANSITION}$



**TEST CIRCUIT 7**  
CHARGE INJECTION

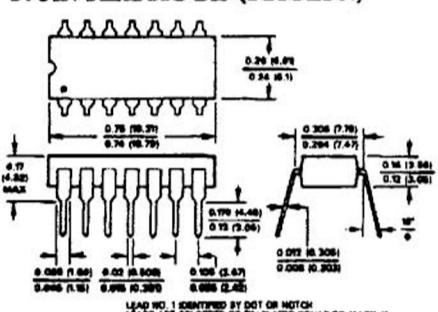


## AD7590DI/AD7591DI/AD7592DI

### MECHANICAL INFORMATION OUTLINE DIMENSIONS

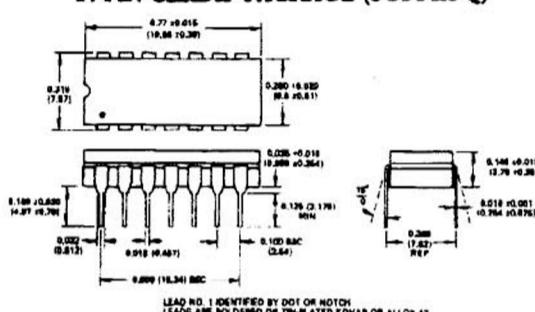
Dimensions shown in inches and (mm).

**14-PIN PLASTIC DIP (SUFFIX N)**



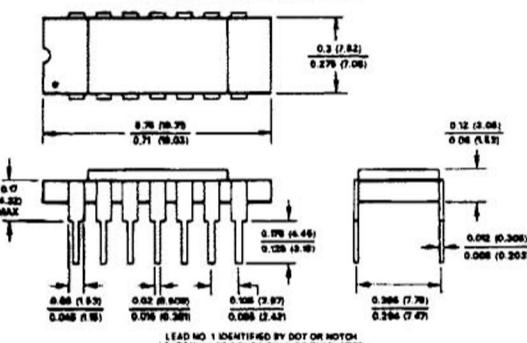
**AD7592DI**

**14-PIN CERDIP PACKAGE (SUFFIX Q)**



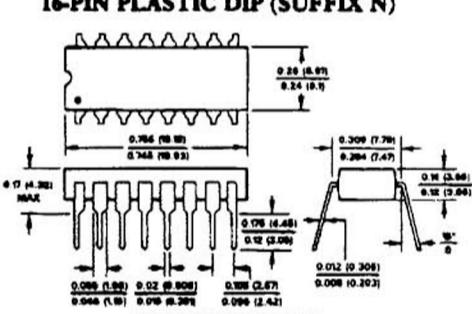
**AD7592DI**

**14-PIN CERAMIC DIP\***



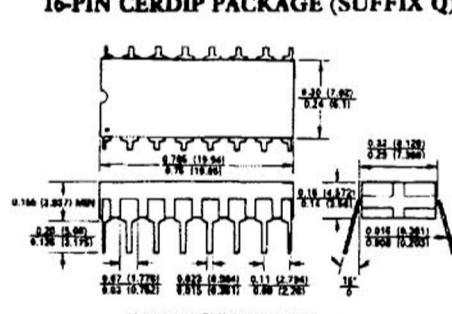
**AD7592DI**

**16-PIN PLASTIC DIP (SUFFIX N)**



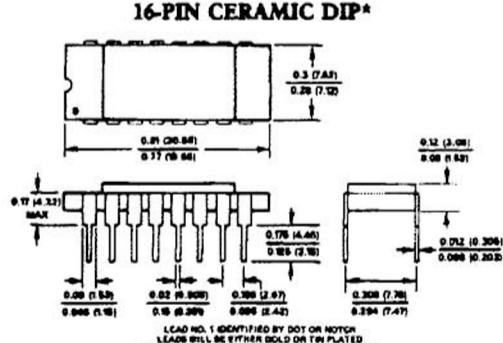
**AD7590DI, AD7591DI**

**16-PIN CERDIP PACKAGE (SUFFIX Q)**



**AD7590DI, AD7591DI**

**16-PIN CERAMIC DIP\***



**AD7590DI, AD7591DI**

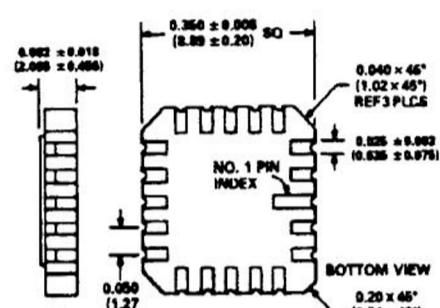
\*ANALOG DEVICES RESERVES TO RIGHT TO SHIP CERAMIC PACKAGES IN LIEU OF CERDIP PACKAGES.

# AD7590DI/AD7591DI/AD7592DI

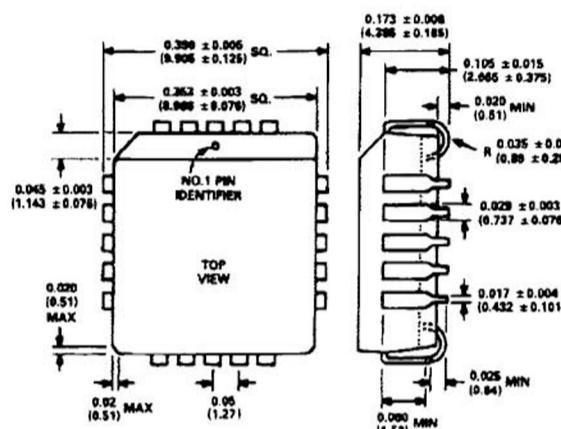
## OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

**20-Terminal Leadless Ceramic Chip Carrier (Suffix E)**

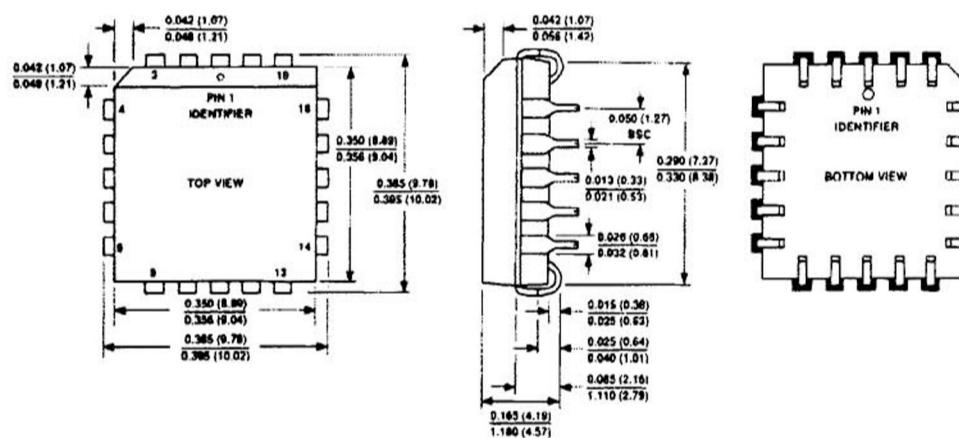


**20-Terminal Plastic Leaded Chip Carrier (Suffix P)**



C517c-21-11/86

**PLCC (P-20A)**



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